

## SMALL SIGNAL PNP TRANSISTOR

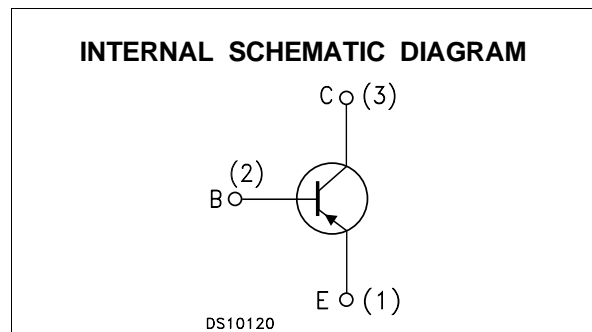
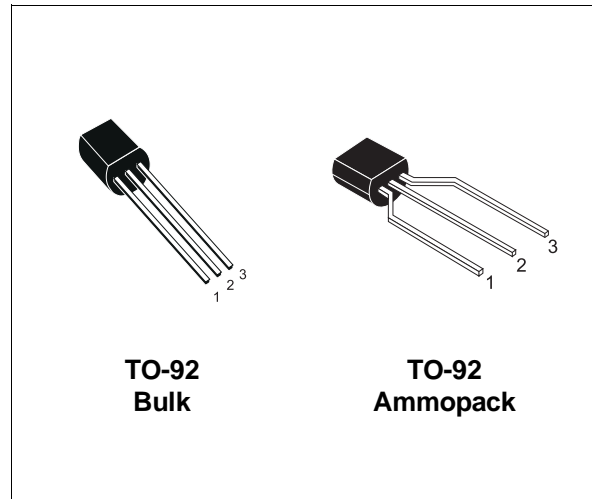
### PRELIMINARY DATA

Ordering Code	Marking	Package / Shipment
2N3906	2N3906	TO-92 / Bulk
2N3906-AP	2N3906	TO-92 / Ammopack

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- THE PNP COMPLEMENTARY TYPE IS 2N3904

### APPLICATIONS

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	-60	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	-40	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	-6	V
$I_C$	Collector Current	-200	mA
$P_{tot}$	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	625	mW
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

## THERMAL DATA

R <sub>thj-amb</sub> •	Thermal Resistance Junction-Ambient	Max	200	°C/W
R <sub>thj-Case</sub> •	Thermal Resistance Junction-Case	Max	83.3	°C/W

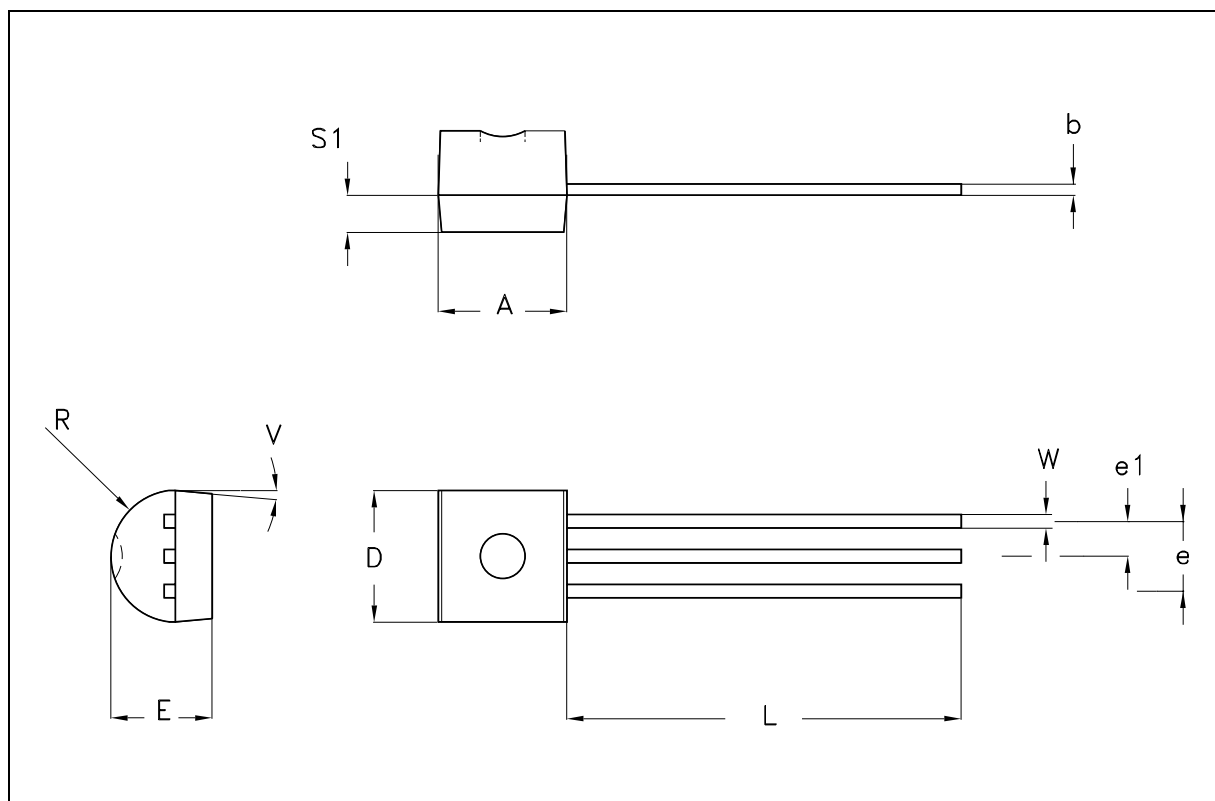
ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CEX</sub>	Collector Cut-off Current (V <sub>BE</sub> = 3 V)	V <sub>CE</sub> = -30 V			-50	nA
I <sub>BEX</sub>	Base Cut-off Current (V <sub>BE</sub> = 3 V)	V <sub>CE</sub> = -30 V			-50	nA
V <sub>(BR)CEO</sub> *	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = -1 mA	-40			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -10 μA	-60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = -10 μA	-6			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10 mA I <sub>B</sub> = -1 mA I <sub>C</sub> = -50 mA I <sub>B</sub> = -5 mA			-0.25 -0.4	V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = -10 mA I <sub>B</sub> = -1 mA I <sub>C</sub> = -50 mA I <sub>B</sub> = -5 mA	-0.65		-0.85 -0.95	V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = -0.1 mA V <sub>CE</sub> = -1 V I <sub>C</sub> = -1 mA V <sub>CE</sub> = -1 V I <sub>C</sub> = -10 mA V <sub>CE</sub> = -1 V I <sub>C</sub> = -50 mA V <sub>CE</sub> = -1 V I <sub>C</sub> = -100 mA V <sub>CE</sub> = -1 V	60 80 100 60 30		300	
f <sub>T</sub>	Transition Frequency	I <sub>C</sub> = -10mA V <sub>CE</sub> = -20 V f = 100 MHz	250			MHz
NF	Noise Figure	V <sub>CE</sub> = -5 V I <sub>C</sub> = -0.1 mA f = 10 Hz to 15.7 KHz R <sub>G</sub> = 1 KΩ		4		dB
C <sub>CBO</sub>	Collector-Base Capacitance	I <sub>E</sub> = 0 V <sub>CB</sub> = -5 V f = 100 KHz		6		pF
C <sub>EBO</sub>	Emitter-Base Capacitance	I <sub>C</sub> = 0 V <sub>EB</sub> = -0.5 V f = 100 KHz		25		pF
t <sub>d</sub>	Delay Time	I <sub>C</sub> = -10 mA I <sub>B</sub> = -1 mA			35	ns
t <sub>r</sub>	Rise Time	V <sub>CC</sub> = -3V			35	ns
t <sub>s</sub>	Storage Time	I <sub>C</sub> = -10 mA I <sub>B1</sub> = -I <sub>B2</sub> = -1 mA			225	ns
t <sub>f</sub>	Fall Time	V <sub>CC</sub> = -3V			72	ns

\* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

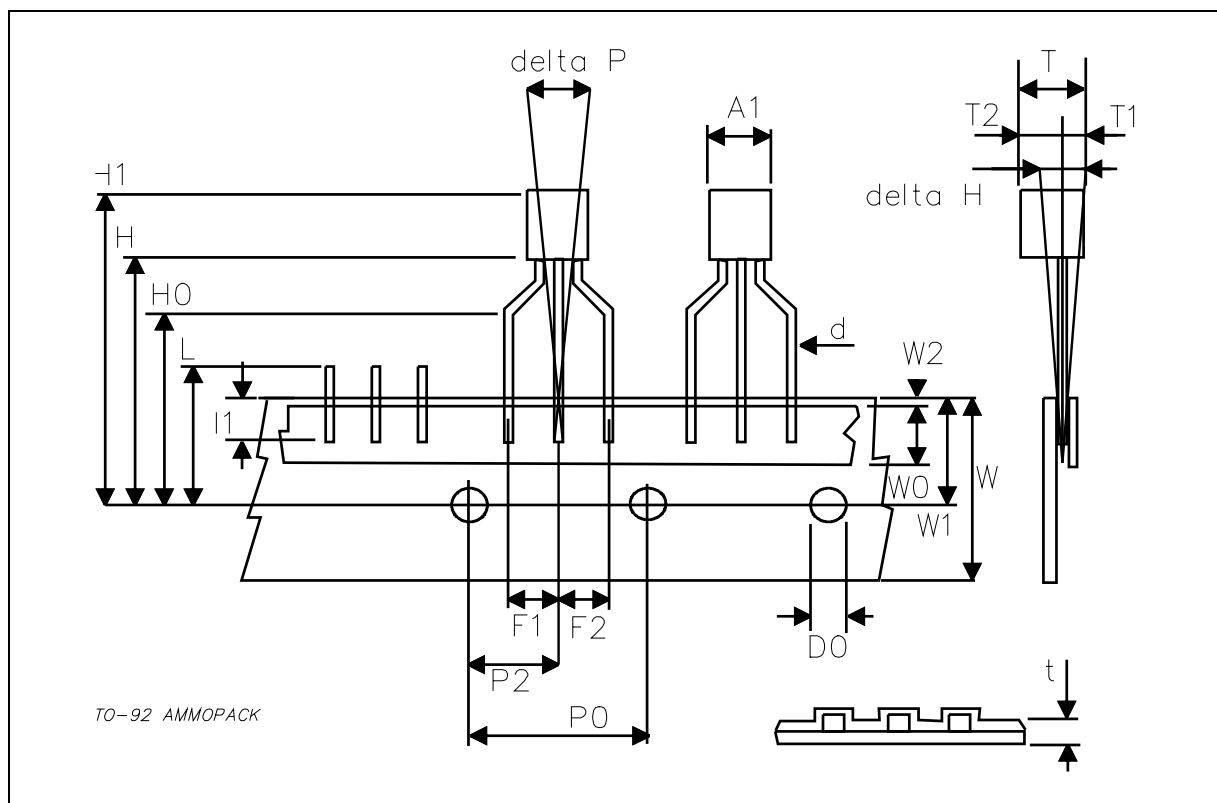
## TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



**TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A1			4.80			0.189
T			3.80			0.150
T1			1.60			0.063
T2			2.30			0.091
d			0.48			0.019
P0	12.50	12.70	12.90	0.492	0.500	0.508
P2	5.65	6.35	7.05	0.222	0.250	0.278
F1,F2	2.44	2.54	2.94	0.096	0.100	0.116
delta H	-2.00		2.00	-0.079		0.079
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.70	6.00	6.30	0.224	0.236	0.248
W1	8.50	9.00	9.25	0.335	0.354	0.364
W2			0.50			0.020
H	18.50		20.50	0.728		0.807
H0	15.50	16.00	16.50	0.610	0.630	0.650
H1			25.00			0.984
D0	3.80	4.00	4.20	0.150	0.157	0.165
t			0.90			0.035
L			11.00			0.433
I1	3.00			0.118		
delta P	-1.00		1.00	-0.039		0.039



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